DATA SHEET

NEC

BIPOLAR ANALOG INTEGRATED CIRCUIT

μPC3226TB

5 V, SILICON GERMANIUM MMIC MEDIUM OUTPUT POWER AMPLIFIER

DESCRIPTION

The μPC3226TB is a silicon germanium (SiGe) monolithic integrated circuit designed as IF amplifier for DBS tuners. This IC is manufactured using our 50 GHz f_{max} UHS2 (Ultra High Speed Process) SiGe bipolar process.

FEATURES

- Low current : I_{CC} = 15.5 mA TYP. @ V_{CC} = 5.0 V
- Medium output power : $P_{O (sat)}$ = +13.0 dBm TYP. @ f = 1.0 GHz
  : $P_{O (sat)}$ = +9.0 dBm TYP. @ f = 2.2 GHz
- High linearity : $P_{O (1dB)}$ = +7.5 dBm TYP. @ f = 1.0 GHz
  : $P_{O (1dB)}$ = +5.7 dBm TYP. @ f = 2.2 GHz
- Power gain : G_P = 25.0 dB TYP. @ f = 1.0 GHz
  : G_P = 26.0 dB TYP. @ f = 2.2 GHz
- Noise Figure : NF = 5.3 dB TYP. @ f = 1.0 GHz
  : NF = 4.9 dB TYP. @ f = 2.2 GHz
- Supply voltage : V_{CC} = 4.5 to 5.5 V
- Port impedance : input/output 50 Ω

APPLICATIONS

- IF amplifiers in LNB for DBS converters etc.

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPC3226TB-E3	μPC3226TB-E3-A	6-pin super minimold (Pb-Free) Note	C3N	Embossed tape 8 mm wide. 1, 2, 3 pins face the perforation side of the tape. Qty 3 kpcs/reel.

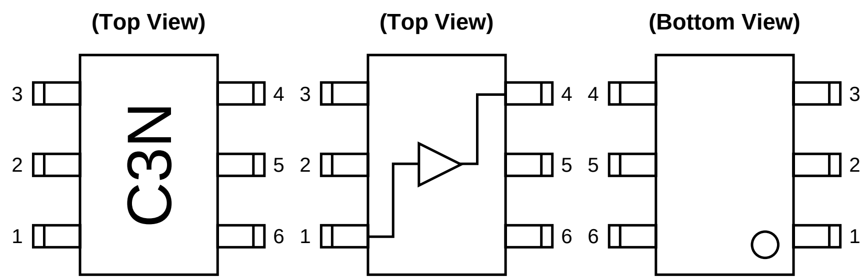
Note With regards to terminal solder (the solder contains lead) plated products (conventionally plated), contact your nearby sales office.

Remark To order evaluation samples, please contact your nearby sales office
Part number for sample order: μPC3226TB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

Document No. PU10558EJ01V0DS (1st edition)
Date Published May 2005 CP(K)
Printed in Japan

PIN CONNECTIONS



Pin No.	Pin Name
1	INPUT
2	GND
3	GND
4	OUTPUT
5	GND
6	V_{CC}

PRODUCT LINE-UP OF 5 V-BIAS SILICON MMIC MEDIUM OUTPUT POWER AMPLIFIER
(T_A = +25°C, f = 1 GHz, V_{CC} = V_{out} = 5.0 V, Z_S = Z_L = 50 Ω)

Part No.	f_u (GHz)	$P_{O (sat)}$ (dBm)	G_P (dB)	NF (dB)	I_{CC} (mA)	Package	Marking
μPC2708TB	2.9	+10.0	15	6.5	26	6-pin super minimold	C1D
μPC2709TB	2.3	+11.5	23	5.0	25		C1E
μPC2710TB	1.0	+13.5	33	3.5	22		C1F
μPC2776TB	2.7	+8.5	23	6.0	25		C2L
μPC3223TB	3.2	+12.0	23	4.5	19		C3J
μPC3225TB	2.8	+15.5 Note	32.5 Note	3.7 Note	24.5		C3M
μPC3226TB	3.2	+13.0	25	5.3	15.5		C3N

Note μPC3225TB is f = 0.95 GHz

Remark Typical performance. Please refer to **ELECTRICAL CHARACTERISTICS** in detail.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	V_{CC}	T_A = +25°C	6.0	V
Total Circuit Current	I_{CC}	T_A = +25°C	40	mA
Power Dissipation	P_D	T_A = +85°C **Note**	270	mW
Operating Ambient Temperature	T_A		–40 to +85	°C
Storage Temperature	T_{stg}		–55 to +150	°C
Input Power	P_{in}	T_A = +25°C	+10	dBm

Note Mounted on double-sided copper-clad 50 × 50 × 1.6 mm epoxy glass PWB

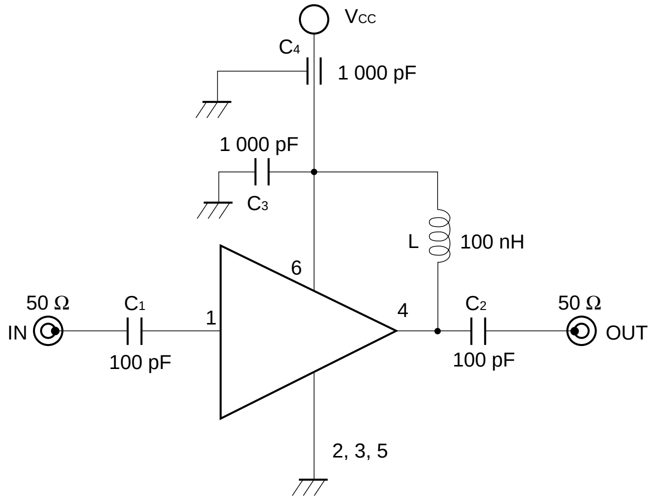
RECOMMENDED OPERATING RANGE

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply Voltage	V_{CC}		4.5	5.0	5.5	V
Operating Ambient Temperature	T_A		–40	+25	+85	°C

ELECTRICAL CHARACTERISTICS (T_A = +25°C, V_{CC} = V_{out} = 5.0 V, Z_S = Z_L = 50 Ω)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	I_{CC}	No input signal	12.5	15.5	19.5	mA
Power Gain 1	G_P1	f = 0.1 GHz, P_{in} = –30 dBm	22.0	24.0	26.0	dB
Power Gain 2	G_P2	f = 1.0 GHz, P_{in} = –30 dBm	23.0	25.0	27.5	
Power Gain 3	G_P3	f = 1.8 GHz, P_{in} = –30 dBm	23.0	26.0	29.0	
Power Gain 4	G_P4	f = 2.2 GHz, P_{in} = –30 dBm	23.0	26.0	29.0	
Power Gain 5	G_P5	f = 2.6 GHz, P_{in} = –30 dBm	22.5	25.5	29.0	
Power Gain 6	G_P6	f = 3.0 GHz, P_{in} = –30 dBm	22.0	25.0	28.5	
Saturated Output Power 1	$P_{O (sat)}1$	f = 1.0 GHz, P_{in} = –2 dBm	+10.0	+13.0	–	dBm
Saturated Output Power 2	$P_{O (sat)}2$	f = 2.2 GHz, P_{in} = –8 dBm	+6.0	+9.0	–	
Gain 1 dB Compression Output Power 1	$P_{O (1 dB)}1$	f = 1.0 GHz	+5.0	+7.5	–	dBm
Gain 1 dB Compression Output Power 2	$P_{O (1 dB)}2$	f = 2.2 GHz	+3.0	+5.7	–	
Noise Figure 1	NF1	f = 1.0 GHz	–	5.3	6.0	dB
Noise Figure 2	NF2	f = 2.2 GHz	–	4.9	6.0	
Isolation 1	ISL1	f = 1.0 GHz, P_{in} = –30 dBm	31	34	–	dB
Isolation 2	ISL2	f = 2.2 GHz, P_{in} = –30 dBm	33	36	–	
Input Return Loss 1	$RL_{in}1$	f = 1.0 GHz, P_{in} = –30 dBm	10.0	14.0	–	dB
Input Return Loss 2	$RL_{in}2$	f = 2.2 GHz, P_{in} = –30 dBm	9.0	13.0	–	
Output Return Loss 1	$RL_{out}1$	f = 1.0 GHz, P_{in} = –30 dBm	10.0	13.0	–	dB
Output Return Loss 2	$RL_{out}2$	f = 2.2 GHz, P_{in} = –30 dBm	10.0	13.0	–	
Input 3rd Order Distortion Intercept Point 1	IIP_31	f1 = 1 000 MHz, f2 = 1 001 MHz, P_{in} = –30 dBm	–	–5.0	–	dBm
Input 3rd Order Distortion Intercept Point 2	IIP_32	f1 = 2 200 MHz, f2 = 2 201 MHz, P_{in} = –30 dBm	–	–11.0	–	
Output 3rd Order Distortion Intercept Point 1	OIP_31	f1 = 1 000 MHz, f2 = 1 001 MHz, P_{in} = –30 dBm	–	+20.0	–	dBm
Output 3rd Order Distortion Intercept Point 2	OIP_32	f1 = 2 200 MHz, f2 = 2 201 MHz, P_{in} = –30 dBm	–	+15.0	–	
2nd Order Intermodulation Distortion	IM_2	f1 = 1 000 MHz, f2 = 1 001 MHz, P_{in} = –30 dBm	–	43.0	–	dBc
K factor 1	K1	f = 1.0 GHz	–	1.4	–	–
K factor 2	K2	f = 2.2 GHz	–	1.6	–	–

TEST CIRCUIT



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

	Type	Value
C1, C2	Chip Capacitor	100 pF
C3	Chip Capacitor	1 000 pF
C4	Feed-through Capacitor	1 000 pF
L	Chip Inductor	100 nH

INDUCTOR FOR THE OUTPUT PIN

The internal output transistor of this IC, to output medium power. To supply current for output transistor, connect an inductor between the V_{CC} pin (pin 6) and output pin (pin 4). Select inductance, as the value listed above.

The inductor has both DC and AC effects. In terms of DC, the inductor biases the output transistor with minimum voltage drop to output enable high level. In terms of AC, the inductor makes output-port impedance higher to get enough gain. In this case, large inductance and Q is suitable.

CAPACITORS FOR THE V_{CC}, INPUT AND OUTPUT PINS

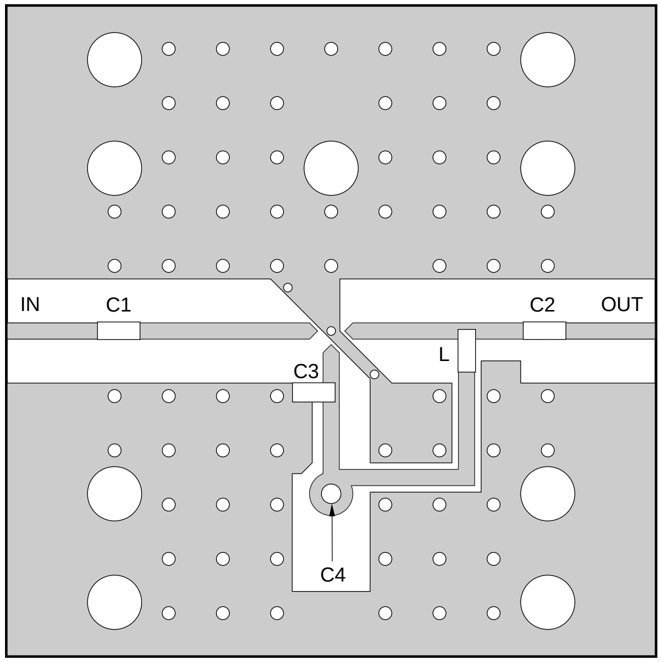
Capacitors of 1 000 pF are recommendable as the bypass capacitor for the V_{CC} pin and the coupling capacitors for the input and output pins.

The bypass capacitor connected to the V_{CC} pin is used to minimize ground impedance of V_{CC} pin. So, stable bias can be supplied against V_{CC} fluctuation.

The coupling capacitors, connected to the input and output pins, are used to cut the DC and minimize RF serial impedance. Their capacitances are therefore selected as lower impedance against a 50 Ω load. The capacitors thus perform as high pass filters, suppressing low frequencies to DC.

To obtain a flat gain from 100 MHz upwards, 1 000 pF capacitors are used in the test circuit. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 10 000 pF. Because the coupling capacitors are determined by equation, $C = 1/(2\pi Rfc)$.

ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



COMPONENT LIST

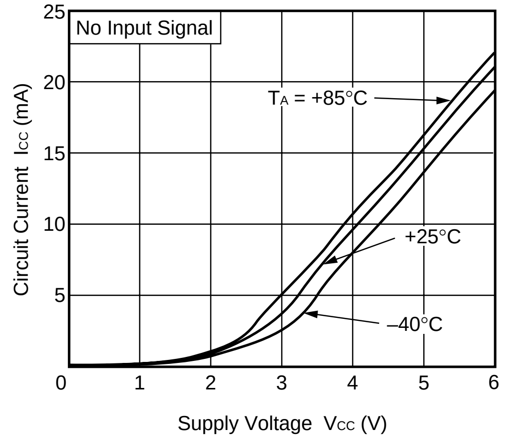
	Value
C1, C2	100 pF
C3, C4	1 000 pF
L1	100 nH

Notes

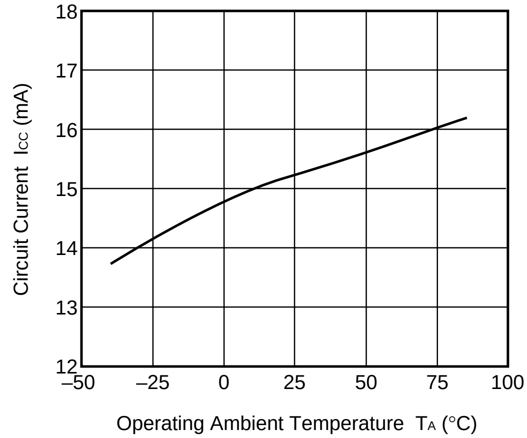
1. 30 × 30 × 0.4 mm double sided copper clad polyimide board.
2. Back side: GND pattern
3. Solder plated on pattern
4. ○◯: Through holes

TYPICAL CHARACTERISTICS (T_A = +25°C, V_{CC} = V_{out} = 5.0 V, Z_S = Z_L = 50 Ω, unless otherwise specified)

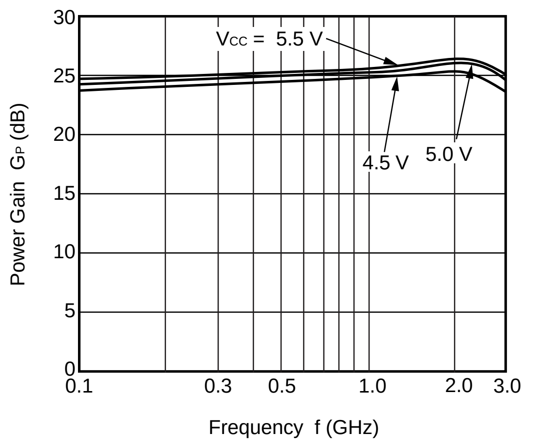
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



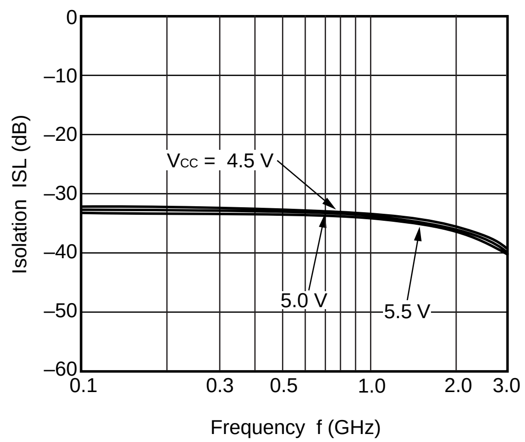
CURCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE



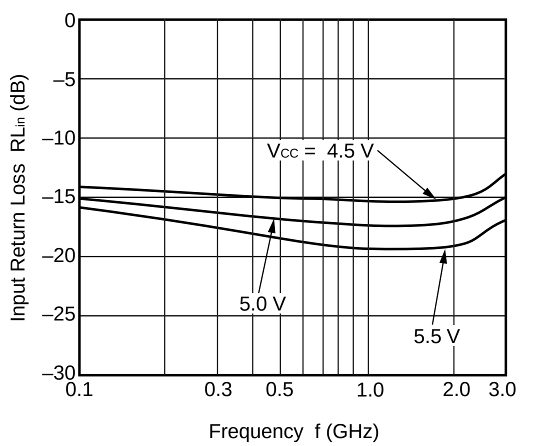
POWER GAIN vs. FREQUENCY



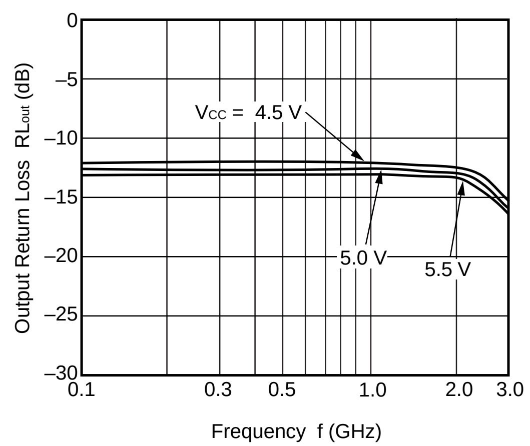
ISOLATION vs. FREQUENCY



INPUT RETURN LOSS vs. FREQUENCY

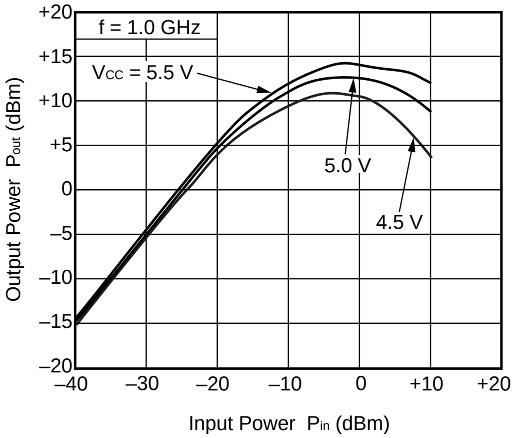


OUTPUT RETURN LOSS vs. FREQUENCY

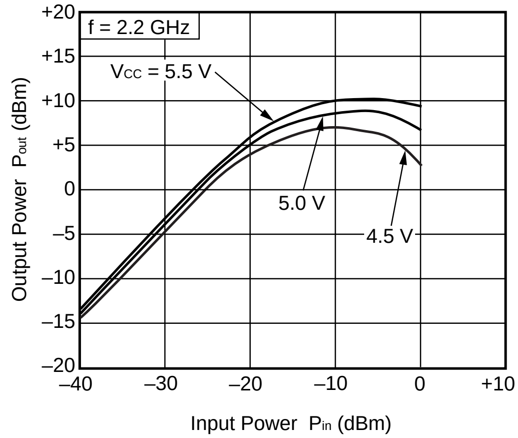


Remark The graphs indicate nominal characteristics.

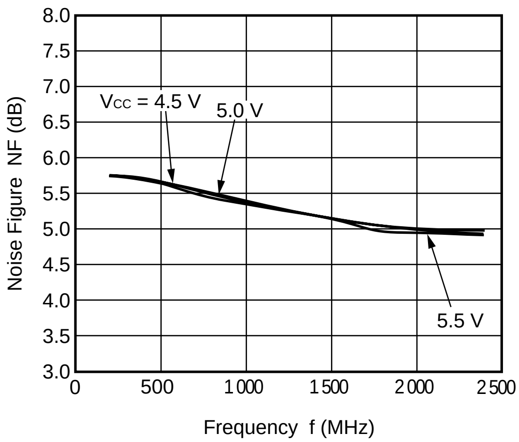
OUTPUT POWER vs. INPUT POWER



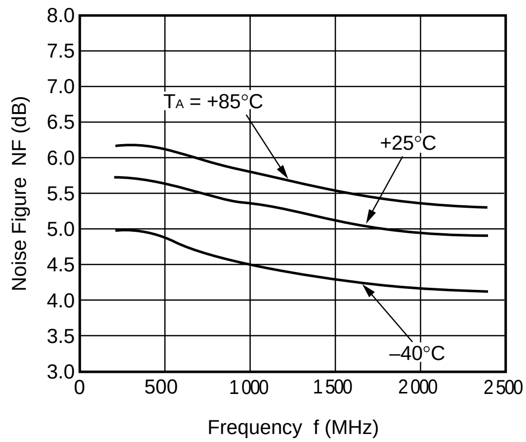
OUTPUT POWER vs. INPUT POWER



NOISE FIGURE vs. FREQUENCY

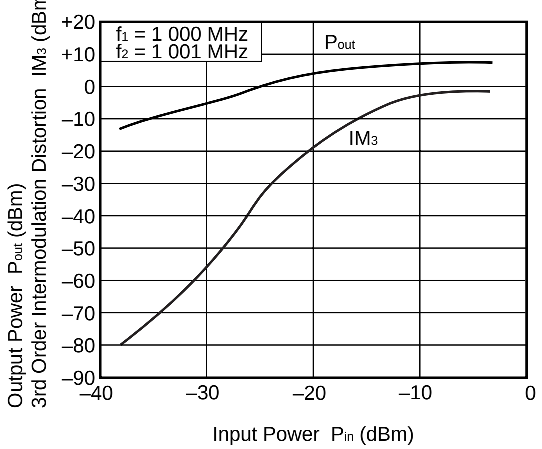


NOISE FIGURE vs. FREQUENCY

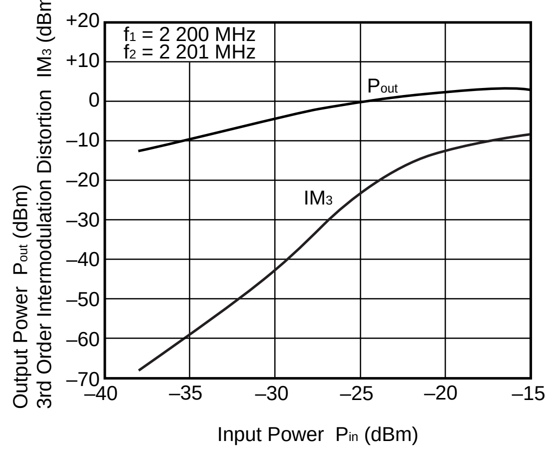


Remark The graphs indicate nominal characteristics.

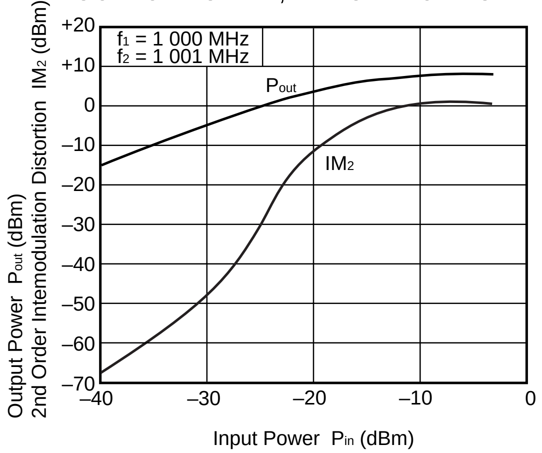
OUTPUT POWER, IM3 vs. INPUT POWER



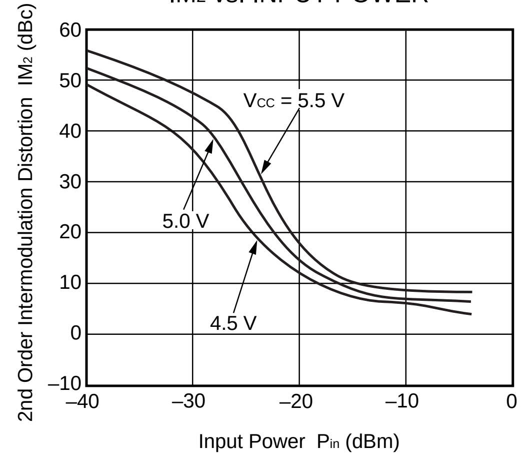
OUTPUT POWER, IM3 vs. INPUT POWER



OUTPUT POWER, IM2 vs. INPUT POWER



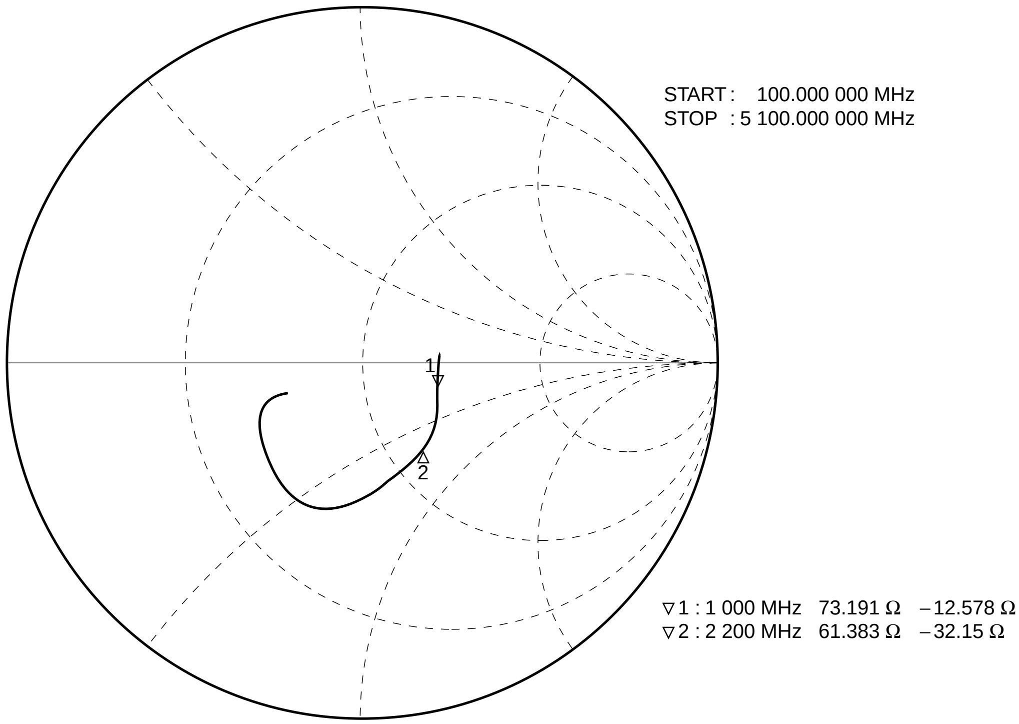
IM2 vs. INPUT POWER



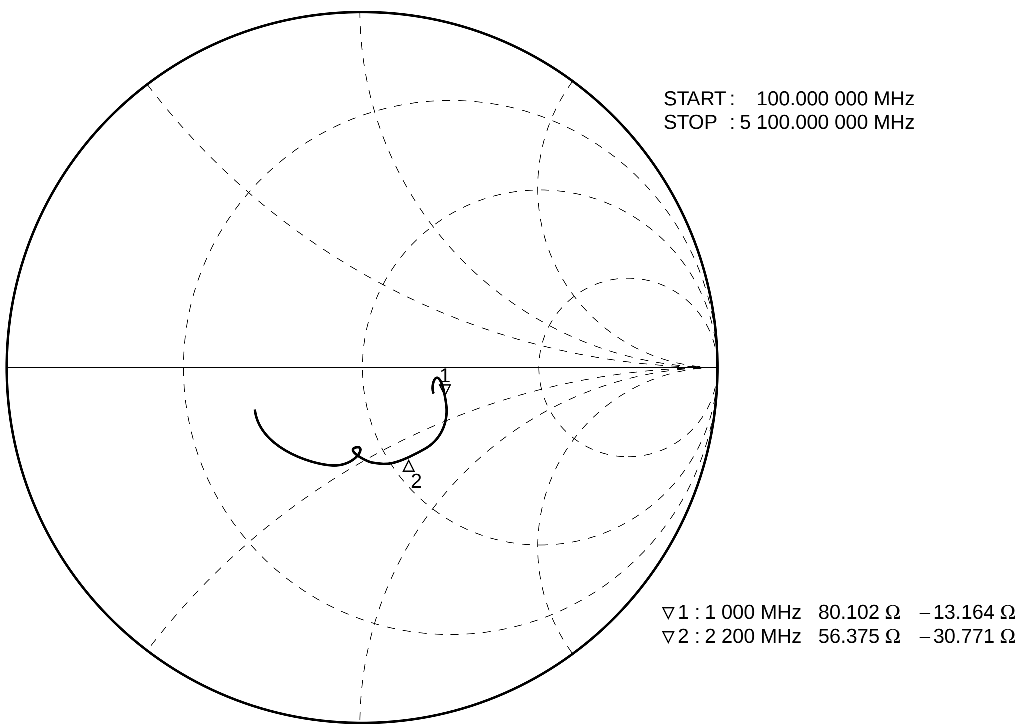
Remark The graphs indicate nominal characteristics.

S-PARAMETERS (T_A = +25°C, V_{CC} = V_{out} = 5.0 V, P_{in} = –30 dBm)

S_{11}–FREQUENCY

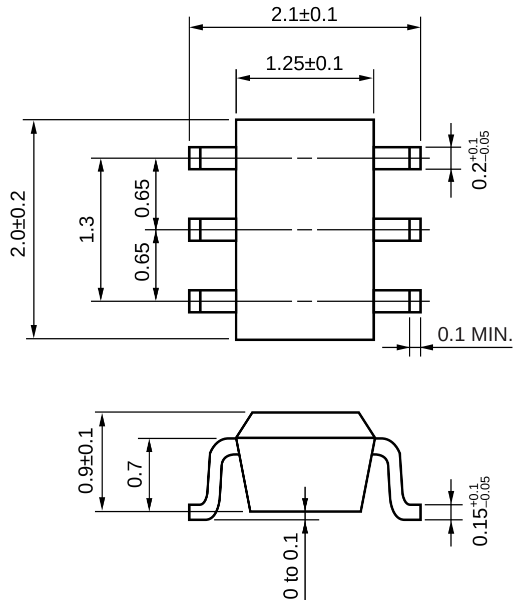


S_{22}–FREQUENCY



PACKAGE DIMENSIONS

6-PIN SUPER MINIMOLD (UNIT: mm)



NOTES ON CORRECT USE

(1) Observe precautions for handling because of electro-static sensitive devices.

(2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground terminals must be connected together with wide ground pattern to decrease impedance difference.

(3) The bypass capacitor should be attached to the V_{CC} line.

(4) The inductor (L) must be attached between V_{CC} and output pins. The inductance value should be determined in accordance with desired frequency.

(5) The DC cut capacitor must be attached to input and output pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature)	: 260°C or below	IR260
	Time at peak temperature	: 10 seconds or less	
	Time at temperature of 220°C or higher	: 60 seconds or less	
	Preheating time at 120 to 180°C	: 120±30 seconds	
	Maximum number of reflow processes	: 3 times	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	
Wave Soldering	Peak temperature (molten solder temperature)	: 260°C or below	WS260
	Time at peak temperature	: 10 seconds or less	
	Preheating temperature (package surface temperature)	: 120°C or below	
	Maximum number of flow processes	: 1 time	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	
Partial Heating	Peak temperature (terminal temperature)	: 350°C or below	HS350
	Soldering time (per side of device)	: 3 seconds or less	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	

Caution Do not use different soldering methods together (except for partial heating).

▶**For further information, please contact**

NEC Compound Semiconductor Devices, Ltd. http://www.ncsd.necel.com/
E-mail: salesinfo@ml.ncsd.necel.com (sales and general)
techinfo@ml.ncsd.necel.com (technical)
Sales Division TEL: +81-44-435-1573 FAX: +81-44-435-1579

NEC Compound Semiconductor Devices Hong Kong Limited
E-mail: ncsd-hk@elhk.nec.com.hk (sales, technical and general)

Hong Kong Head Office	TEL: +852-3107-7303	FAX: +852-3107-7309
Taipei Branch Office	TEL: +886-2-8712-0478	FAX: +886-2-2545-3859
Korea Branch Office	TEL: +82-2-558-2120	FAX: +82-2-558-5209

NEC Electronics (Europe) GmbH http://www.ee.nec.de/
TEL: +49-211-6503-0 FAX: +49-211-6503-1327

California Eastern Laboratories, Inc. http://www.cel.com/
TEL: +1-408-988-3500 FAX: +1-408-988-0279

0504